

# HAT2204C

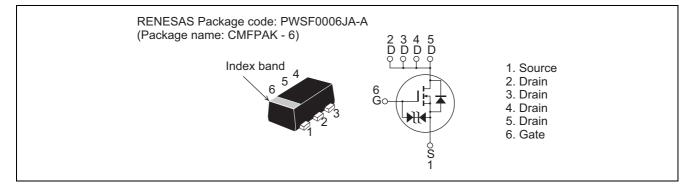
Silicon N Channel MOS FET Power Switching

> REJ03G0448-0500 Rev.5.00 May 10, 2007

# Features

- Low on-resistance  $R_{DS(on)} = 26m \Omega \text{ typ.}(\text{at } V_{GS} = 4.5 \text{ V})$
- Low drive current
- High density mounting
- 1.8 V gate drive device

# Outline



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ Item Symbol Ratings Unit Drain to Source voltage 12 V VDSS V Gate to Source voltage ±8 V<sub>GSS</sub> Drain current 3.5 А  $I_D$ Drain peak current I<sub>D (pulse)</sub> 14 А 3.5 Body - Drain diode reverse Drain current А IDR Pch Note2 Channel dissipation 900 mW Channel temperature 150 °C Tch Storage temperature -55 to +150 °C Tstg

Notes: 1.  $PW \leq 10 \ \mu s, \ duty \ cycle \leq 1\%$ 

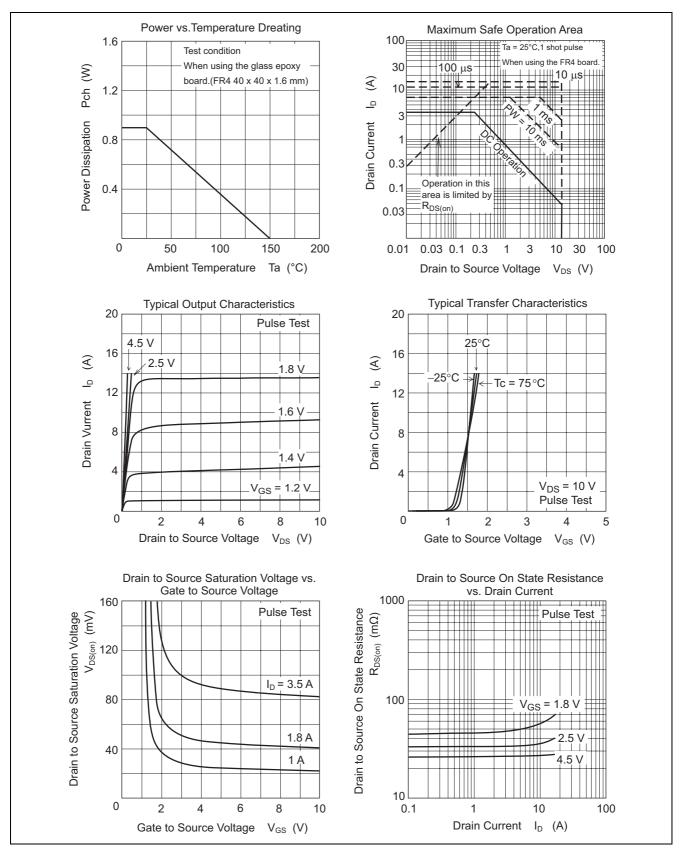
2. When using the glass epoxy board (FR4 40 x 40 x 1.6mm)

# **Electrical Characteristics**

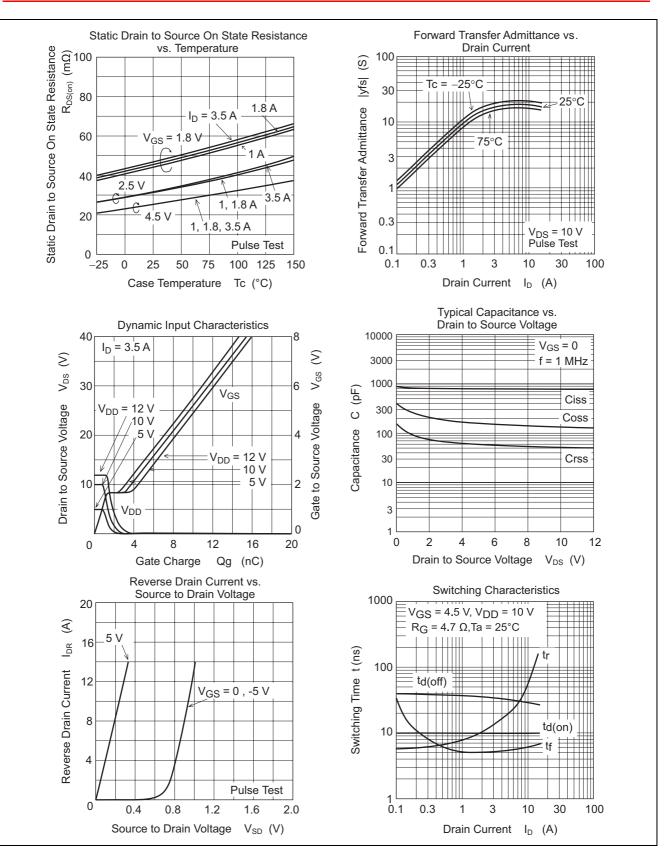
						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to Source breakdown voltage	V <sub>(BR)DSS</sub>	12	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to Source breakdown voltage	V <sub>(BR)GSS</sub>	±8				$I_G = \pm 10 \ \mu\text{A}, \ V_{\text{DS}} = 0$
Gate to Source leakage current	I <sub>GSS</sub>	_	—	±10	μΑ	$V_{GS} = \pm 6.4 \text{ V}, V_{DS} = 0$
Drain to Source leakage current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 12 V, V_{GS} = 0$
Gate to Source cutoff voltage	V <sub>GS(off)</sub>	0.3	_	1.2	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Drain to Source on state resistance	R <sub>DS(on)</sub>		26	34	mΩ	$I_D = 1.8 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note3}}$
	R <sub>DS(on)</sub>		34	44	mΩ	$I_D = 1.8 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note3}}$
	R <sub>DS(on)</sub>	_	45	69	mΩ	$I_D = 1.8 \text{ A}, V_{GS} = 1.8 \text{ V}^{\text{Note3}}$
Forward transfer admittance	yfs	8.5	13		S	$I_D = 1.8 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	770	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss		115	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	50	—	pF	f = 1 MHz
Turn - on delay time	t <sub>d(on)</sub>	—	10	—	ns	$I_D = 1.8 \text{ A}, V_{GS} = 4.5 \text{ V}$
Rise time	tr		9.5	—	ns	$V_{DS}$ = 10 V, $R_{L}$ = 5.6 $\Omega$ ,
Turn - off delay time	t <sub>d(off)</sub>	—	36	—	ns	Rg = 4.7 Ω
Fall time	t <sub>f</sub>		5	—	ns	
Total Gate charge	Qg		9	—	nC	V <sub>DD</sub> = 10 V
Gate to Source charge	Qgs	_	1.5		nC	V <sub>GS</sub> = 4.5 V
Gate to Drain charge	Qgd	_	2		nC	I <sub>D</sub> = 3.5 A
Body - Drain diode forward voltage	V <sub>DF</sub>		0.8	1.1	V	$I_F = 3.5 \text{ A}, V_{GS} = 0^{\text{Note3}}$

Notes: 3. Pulse test

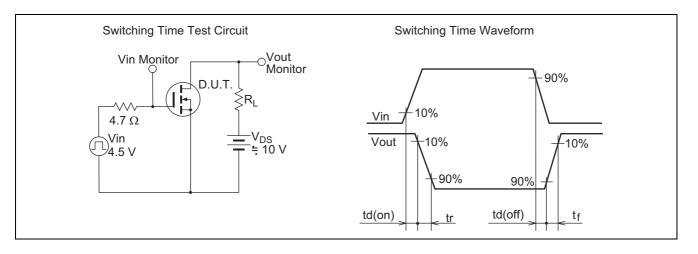
# **Main Characteristics**



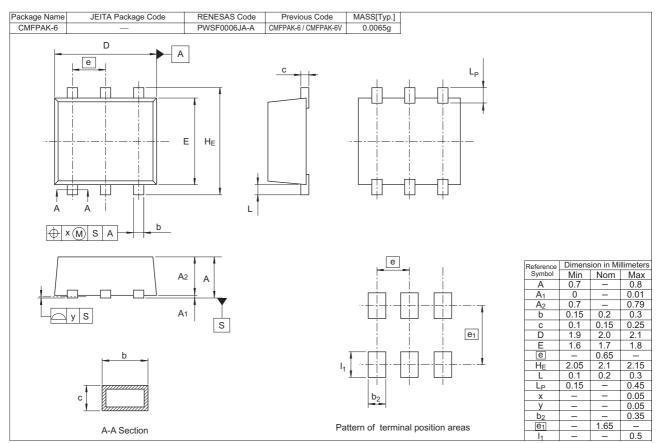
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# **Package Dimensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
HAT2204C-EL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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